

Supplementary information

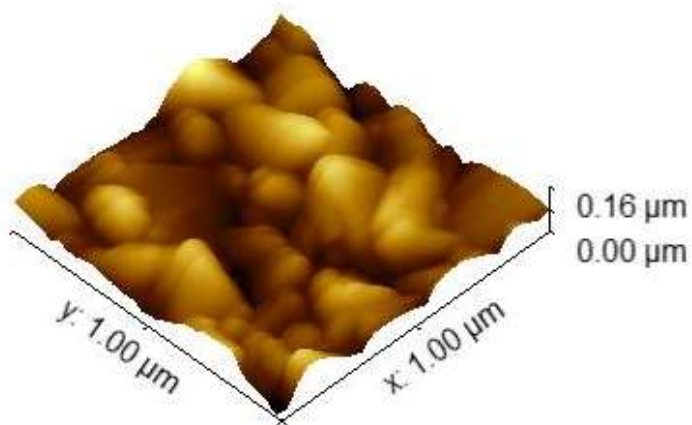
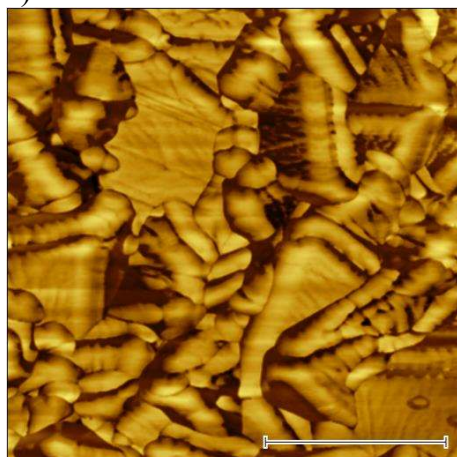
WO₃ Photoanodes for Photoelectrochemical Applications

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a)



b)

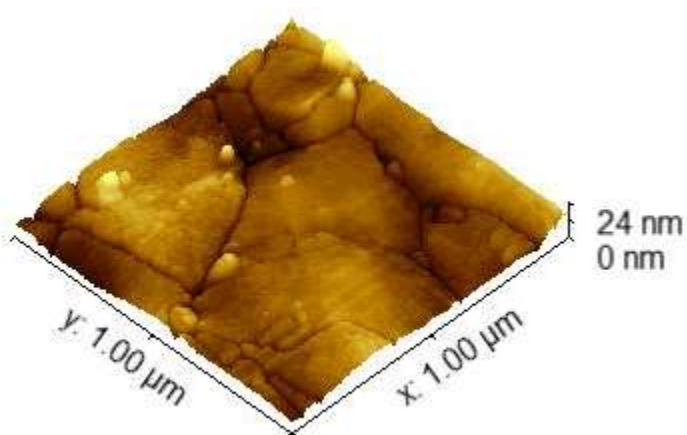
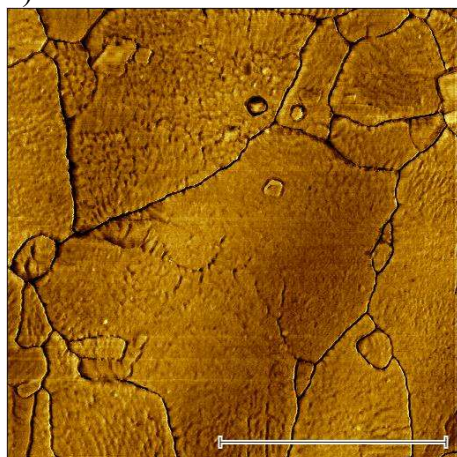


Figure S1. AFM phase images (left) and 3D height AFM images (right) of (a) FTO/glass substrate, (b) 4.2 μm thick WO₃ layer deposited at 250 °C on FTO/glass substrate and post-annealed at 550 °C for 2 h. The black bar in AFM phase images represents 500 nm.

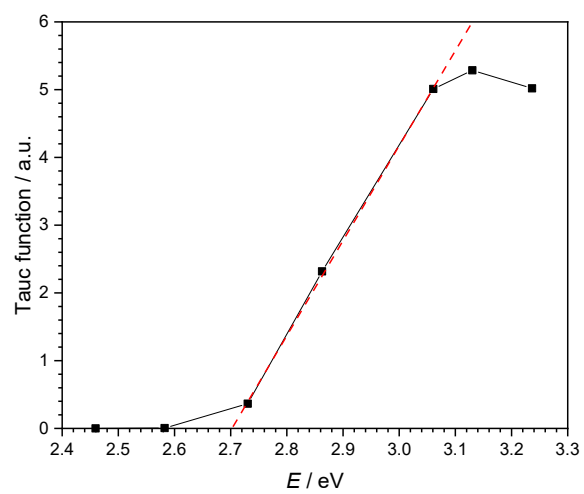


Figure S2. Tauc plot for WO₃ films deposited at 250 °C and post-annealed in air (550 °C, 2 h), layer thickness 4.2 μm .